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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/767,154	01/23/2001	Naoyuki Takahashi	31721-169084 1393		
	590 08/05/2002				
	BAETJER, HOWARI	EXAMINER			
P.O. Box 34385 Washington, DC 20043-9998			SONG, MATTHEW J		
			ART UNIT	PAPER NUMBER	
	•		1765	.<	
			DATE MAILED: 08/05/2002)	

Please find below and/or attached an Office communication concerning this application or proceeding.

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		Application No.		Applicant(s)				
Office Action Summer		09/767,154		TAKAHASHI ET AI				
	Office Action Summary	Examiner		Art Unit				
		Matthew J Song		1765				
Period f	The MAILING DATE of this communication app or Reply	ars on the cover sl	h t with the c	orrespondence add	iress			
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely. - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). - Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b). Status								
1) 🗌	Responsive to communication(s) filed on							
2a)□		— · is action is non-final	ì					
3)	Since this application is in condition for allowa			osocution as to the	morito is			
	closed in accordance with the practice under tion of Claims				e ments is			
4)⊠	Claim(s) 1-7 is/are pending in the application.							
4a) Of the above claim(s) <u>3-7</u> is/are withdrawn from consideration.								
5)□	Claim(s) is/are allowed.							
	6)⊠ Claim(s) <u>1-2</u> is/are rejected.							
	Claim(s) is/are objected to.							
·	Claim(s) are subject to restriction and/or	r election requireme	ent.					
	ion Papers	·						
9)[The specification is objected to by the Examiner	r.						
10)⊠ The drawing(s) filed on <u>23 January 2001</u> is/are: a)□ accepted or b)⊠ objected to by the Examiner.								
	Applicant may not request that any objection to the	e drawing(s) be held ir	n abeyance. Se	ee 37 CFR 1.85(a).				
11)	The proposed drawing correction filed on	is: a)∏ approved l	b) disappro	ved by the Examine	r.			
If approved, corrected drawings are required in reply to this Office action.								
12) The oath or declaration is objected to by the Examiner.								
Priority (under 35 U.S.C. §§ 119 and 120							
13)🛛	Acknowledgment is made of a claim for foreign	priority under 35 U	.S.C. § 119(a))-(d) or (f).				
a)	☐ All b) ☐ Some * c) ☐ None of:							
	1. Certified copies of the priority documents	s have been receive	ed.					
	2. Certified copies of the priority documents	s have been receive	d in Application	on No				
	3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).							
* See the attached detailed Office action for a list of the certified copies not received.								
14) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).								
 a) The translation of the foreign language provisional application has been received. 15) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121. 								
Attachmen								
2) 🔯 Notic	ce of References Cited (PTO-892) se of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449) Paper No(s)	5) 🔲 No	•	(PTO-413) Paper No(s atent Application (PTO				

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DETAILED ACTION

Election/Restrictions

1. Claims 3-7 are withdrawn from further consideration pursuant to 37 CFR 1.142(b) as being drawn to a nonelected invention, there being no allowable generic or linking claim. Election was made without traverse in Paper No. 4.

Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

3. Claims 1-2 are rejected under 35 U.S.C. 102(b) as being anticipated by Sherman (US 5,916,365).

Sherman discloses the deposition of a thin film of silicon dioxide, where the silicon dioxide is grown monolayer by monolayer in an atomic layer epitaxy deposition process using tetraethoxysilane and reducing it with oxygen atoms (col 7, ln 25-45 and col 1, ln 50-67).

"Even though product-by-process claims are limited by and defined by the process, determination of patentability is based on the product itself. The patentability of a product does not depend on its method of production. If the product in the product-by-process claim is the same as or obvious from a product of the prior art, the claim is unpatentable even though the prior product was made by a different process." In re Thorpe, 777

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F.2d 695, 698, 227 USPQ 964, 966 (Fed. Cir. 1985) MPEP § 2113

Sherman discloses the same product as applicant.

Referring to claim 2, Sherman teaches an epitaxy deposition.

4. Claims 1-2 are rejected under 35 U.S.C. 102(b) as being anticipated by Ohtani et al (US 5,904,770).

Ohtani et al (US 5,904,770) discloses the deposition of a silicon oxide film on a substrate can be fabricated by normal pressure CVD using tetraethoxysilane (TEOS) as the starting gas together with gaseous ozone, where normal pressure CVD reads on applicant's under atmospheric deposition (col 8, ln 35-50).

Ohtani et al is silent to a crystal thin film. It is inherent to Ohtani et al that the deposited thin film is a crystal because Ohtani et al teaches the same method as applicant of depositing tetraethoxysilane on a substrate at the same pressure.

Referring to claim 2, Ohtani et al is silent to a crystal epitaxial thin film. It is inherent to Ohtani et al that the deposited thin film is a crystal epitaxial thin film because Ohtani et al teaches the same method as applicant of depositing tetraethoxysilane on a substrate at the same pressure.

Conclusion

5. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

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compounds are pyrolyzed and deposited on a substrate under atmospheric pressure (col 8, ln 35-

Hochido et al (US 5,932,281) teaches normal pressure CVD means that source

45).

6. Any inquiry concerning this communication or earlier communications from the examiner

should be directed to Matthew J Song whose telephone number is 703-305-4953. The examiner

can normally be reached on M-F 9:00-5:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Benjamin L Utech can be reached on 703-308-3868. The fax phone numbers for the

organization where this application or proceeding is assigned are 703-872-9310 for regular

communications and 703-872-9311 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding

should be directed to the receptionist whose telephone number is 703-308-0661.

Matthew J Song

Examiner

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July 29, 2002

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